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Power Matters[™]

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Overview Diagrams

 Electrical Rating
 Symbol
 Min
 Typ
 Max
 Unit

 Collector to Emitter Saturation Voltage
 V_{CE(sat)}
 0.60
 V

 DC Current Gain
 HFE
 20.00
 100.00

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			60.00	V
Collector Current (dc)	I _C			4.00	А
Collector-Emitter Voltage (Base Open)	V _{CEO}			60.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			5.00	V
Power Dissipation, Total	P _T			25.00	W

This part can be found in the following product categories:

- ▶ Discretes ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ PNP Transistor
- Non-Radiation Hardened Devices ► Transistors ► BJT(BiPolar Junction Transistor) ► NPN Transistor

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